

Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

※ Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

ADVANCE INFORMATION

FJ4B0618ZL

Single P-channel MOS FET

■ Features

- Drain-source On-state Resistance : RDS(on) typ. = 175 mΩ (VGS = -10 V)
- CSP(Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)
- Automotive grade

■ Marking Symbol : 21

■ Packaging

Embossed type (Thermo-compression sealing) : 20,000 pcs / reel (standard)

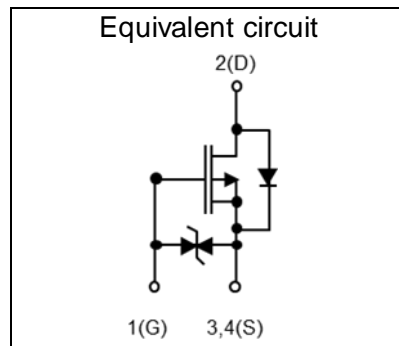
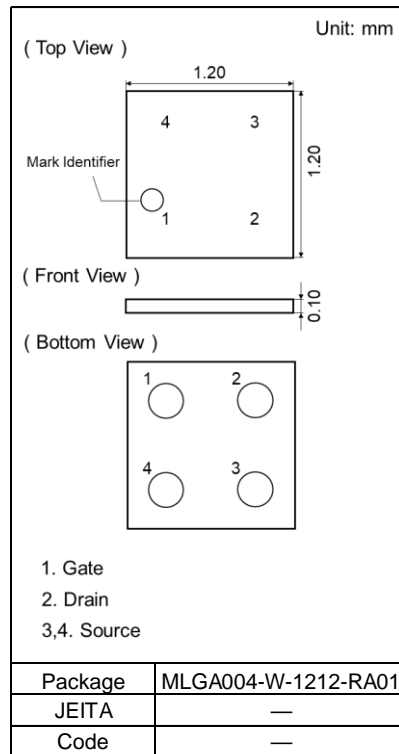
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source Voltage	VDS	-60	V
Gate-source Voltage	VGS	-20 / +10	V
Drain Current	DC	ID ^{*1}	-1.3
		ID ^{*2}	-1.9
		ID ^{*3}	-2.7
	Pulsed ^{*4}	IDp	-15.2
Total Power Dissipation	PD ^{*1}	0.39	W
	PD ^{*2}	0.90	
	PD ^{*3}	1.70	
Operating Junction and Storage Temperature Range	Tj,Tstg	-55 to +150	°C

■ Thermal Characteristics Ta = 25 °C

Parameter	Symbol	Rating	Unit
Thermal Resistance (ch-a)	Rth1 ^{*1}	320	°C / W
	Rth2 ^{*2}	140	
	Rth3 ^{*3}	73	

- Note *1 Mounted on FR4 board (25.4 mm × 25.4 mm × t1.0 mm).
FR4 board partially covered with copper pad (65.4 mm² area, 35 μm thickness).
- *2 Mounted on FR4 board (25.4 mm × 25.4 mm × t1.0 mm).
FR4 board fully covered with copper pad (616 mm² area, 35 μm thickness).
- *3 Mounted on ceramic board (70 mm × 70 mm × t1.0 mm).
- *4 t = 10 μs, Duty Cycle ≤ 1 %.



ADVANCE INFORMATION

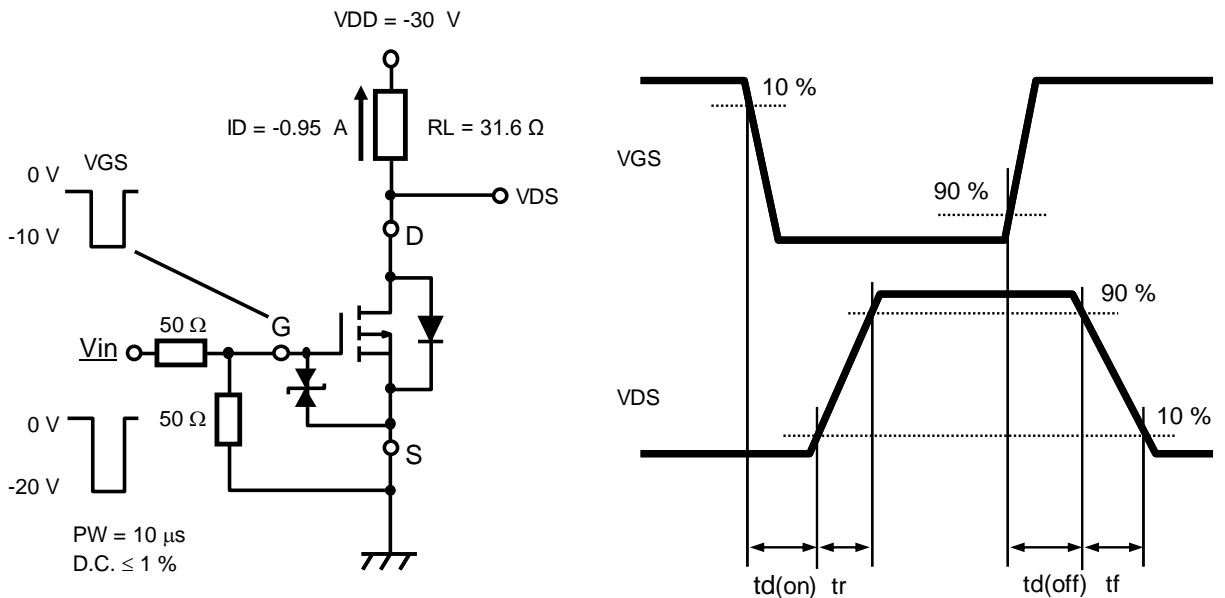
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0 V	-60			V
Zero Gate Voltage Drain Current	IDSS	VDS = -60 V, VGS = 0 V			-1	μA
Gate-source Leakage Current	IGSS	VGS = -16 V, VDS = 0 V			-10	μA
		VGS = +8 V, VDS = 0 V			10	
Gate-source Threshold Voltage	Vth	ID = -3.02 mA, VDS = -10 V	-1		-3	V
Drain-source On-state Resistance	RDS(on)1	ID = -0.95 A, VGS = -10 V	120	175	230	mΩ
	RDS(on)2	ID = -0.95 A, VGS = -4.5 V	130	185	315	
Body Diode Forward Voltage	VF(s-d)	IF = -0.95 A, VGS = 0 V		-0.77	-1.2	V
Input Capacitance ^{*1}	Ciss	VDS = -30 V, VGS = 0 V f = 1 MHz		800		pF
Output Capacitance ^{*1}	Coss			40		
Reverse Transfer Capacitance ^{*1}	Crss			30		
Turn-on Delay Time ^{*1,*2}	td(on)	VDD = -30 V, VGS = 0 to -10 V ID = -0.95 A		9		ns
Rise Time ^{*1,*2}	tr			9		
Turn-off Delay Time ^{*1,*2}	td(off)	VDD = -30 V, VGS = -10 to 0 V ID = -0.95 A		70		
Fall Time ^{*1,*2}	tf			45		
Total Gate Charge ^{*1}	Qg1	VDD = -30 V, VGS = -4.5 V ID = -1.9 A		9		nC
	Qg2			17		
Gate-source Charge ^{*1}	Qgs	VDD = -30 V, VGS = -10 V ID = -1.9 A		2		
Gate-drain Charge ^{*1}	Qgd			3		

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Guaranteed by design, not subject to production testing.

*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time.

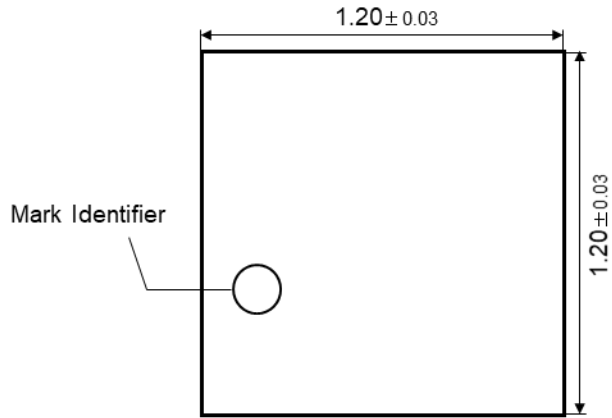


■ ElectroStatic Discharge Characteristics

Standard	Test Type	Symbol	Conditions	Class	Value	Unit
AEC-Q101-001	Human Body Model	HBM	C = 100 pF, R = 1.5 kΩ	H1C	> 1k to ≤ 2k	V

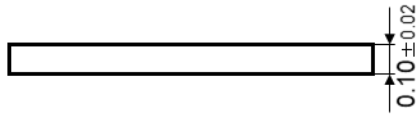
ADVANCE INFORMATION

■ Outline (Top View)

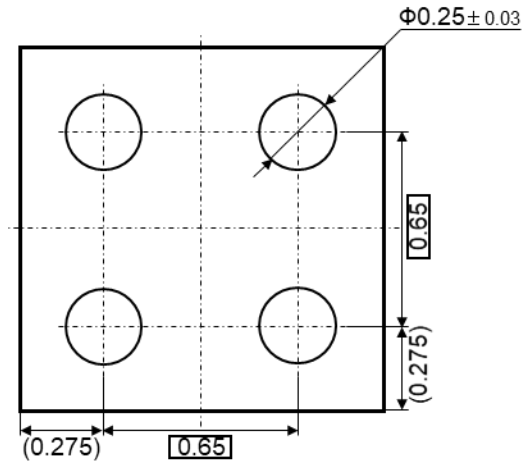


Unit: mm

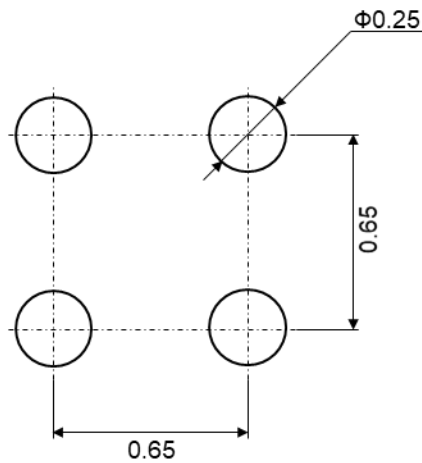
(Front View)



(Bottom View)



■ Land & Stencil Pattern (reference)



Unit: mm

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